

2SK1697

Silicon N-Channel MOS FET

REJ03G1373-0200

(Previous: ADE-208-1313)

Rev.2.00

May 11, 2006

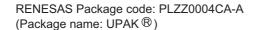
Application

High speed power switching

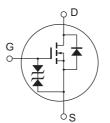
Features

- Low on-resistance
- High speed switching
- Low drive current
- 4 V gate drive device can be driven from 5 V source.
- Suitable for DC DC converter, motor drive, power switch, solenoid drive

Outline







- 1. Gate
- 2. Drain
- 3. Source
- 4. Drain

Note: Marking is "EY".

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Absolute Maximum Ratings

 $(Ta = 25^{\circ}C)$

| Item | Symbol | Ratings | Unit |
|---|--------------------------|-------------|------|
| Drain to source voltage | V_{DSS} | 60 | V |
| Gate to source voltage | V_{GSS} | ±20 | V |
| Drain current | I _D | 0.5 | А |
| Drain peak current | I _{D(pulse)} *1 | 1.5 | А |
| Body to drain diode reverse drain current | I _{DR} | 0.5 | А |
| Channel dissipation | Pch ^{*2} | 1 | W |
| Channel temperature | Tch | 150 | °C |
| Storage temperature | Tstg | -55 to +150 | °C |

Notes: 1. PW \leq 10 μ s, duty cycle \leq 1%

2. When using the alumina ceramic board (12.5 \times 20 \times 0.7 mm)

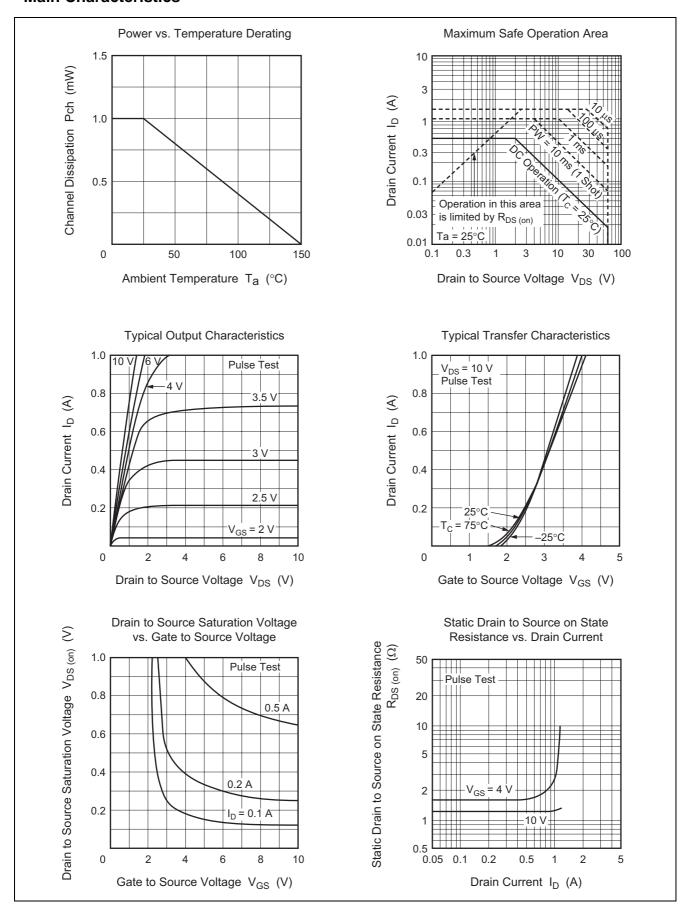
Electrical Characteristics

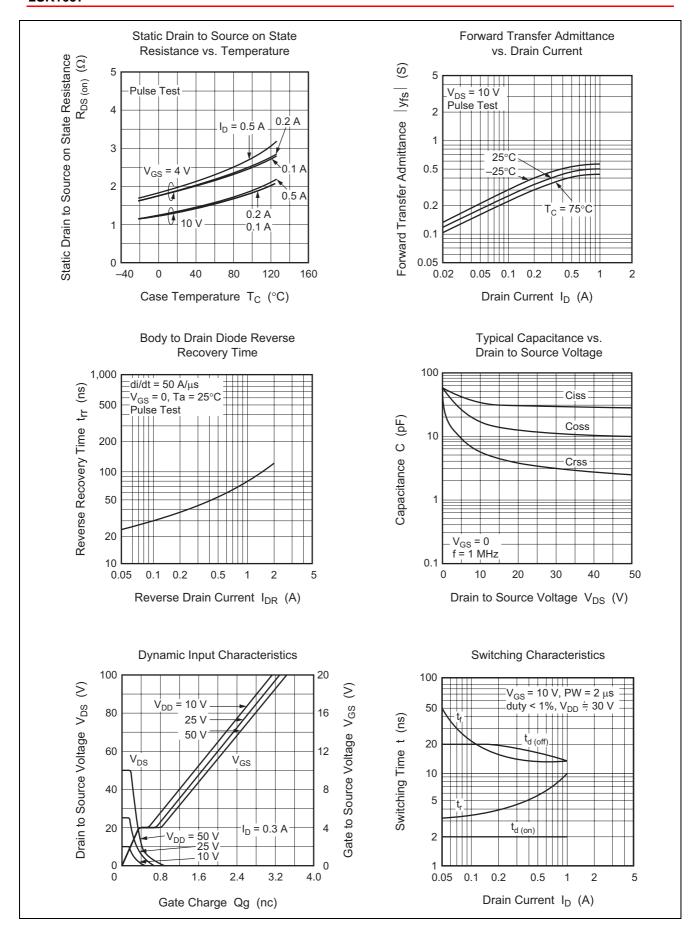
 $(Ta = 25^{\circ}C)$

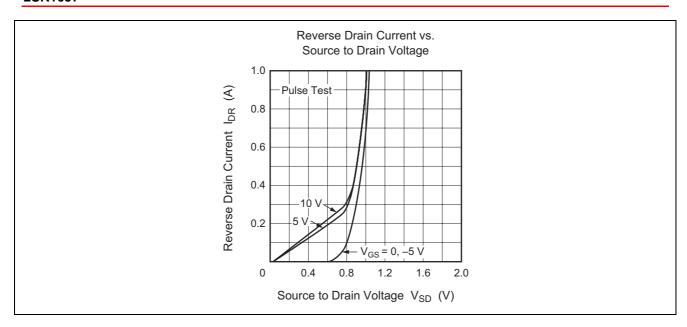
| Item | Symbol | Min | Тур | Max | Unit | Test conditions |
|-------------------------------------|---------------------|------|------|-----|------|---|
| Drain to source breakdown voltage | $V_{(BR)DSS}$ | 60 | _ | _ | V | $I_D = 10 \text{ mA}, V_{GS} = 0$ |
| Gate to source breakdown voltage | $V_{(BR)GSS}$ | ±20 | _ | _ | V | $I_G = \pm 100 \ \mu A, \ V_{DS} = 0$ |
| Gate to source leak current | I_{GSS} | | _ | ±10 | μΑ | $V_{GS} = \pm 16 \text{ V}, V_{DS} = 0$ |
| Zero gate voltage drain current | I _{DSS} | | _ | 50 | μΑ | $V_{DS} = 50 \text{ V}, V_{GS} = 0$ |
| Gate to source cutoff voltage | $V_{GS(off)}$ | 1.0 | _ | 2.0 | V | $I_D = 1 \text{ mA}, V_{DS} = 10 \text{ V}$ |
| Static drain to source on state | R _{DS(on)} | _ | 1.3 | 1.7 | Ω | $I_D = 0.3 \text{ A}, V_{GS} = 10 \text{ V}^{*1}$ |
| resistance | | _ | 1.8 | 2.5 | Ω | $I_D = 0.3 \text{ A}, V_{GS} = 4 \text{ V}^{*1}$ |
| Forward transfer admittance | y _{fs} | 0.25 | 0.38 | _ | S | $I_D = 0.3 \text{ A}, V_{DS} = 10 \text{ V}^{*1}$ |
| Input capacitance | Ciss | _ | 33 | _ | pF | $V_{DS} = 10 \text{ V}, V_{GS} = 0,$ |
| Output capacitance | Coss | _ | 17 | _ | pF | f = 1 MHz |
| Reverse transfer capacitance | Crss | _ | 5 | _ | pF | |
| Turn-on delay time | t _{d(on)} | _ | 3 | _ | ns | $I_D = 0.3 \text{ A}, V_{GS} = 10 \text{ V},$ |
| Rise time | t _r | _ | 8 | _ | ns | $R_L = 100 \Omega$ |
| Turn-off delay time | t _{d(off)} | _ | 18 | _ | ns | |
| Fall time | t _f | _ | 14 | _ | ns | |
| Body to drain diode forward voltage | V_{DF} | _ | 1 | _ | V | $I_F = 0.5 \text{ A}, V_{GS} = 0$ |
| Body to drain diode reverse | t _{rr} | _ | 45 | _ | ns | $I_F = 0.5 \text{ A}, V_{GS} = 0,$ |
| recovery time | | | | | | di _F /dt = 50 A/μs |

Note: 1. Pulse test

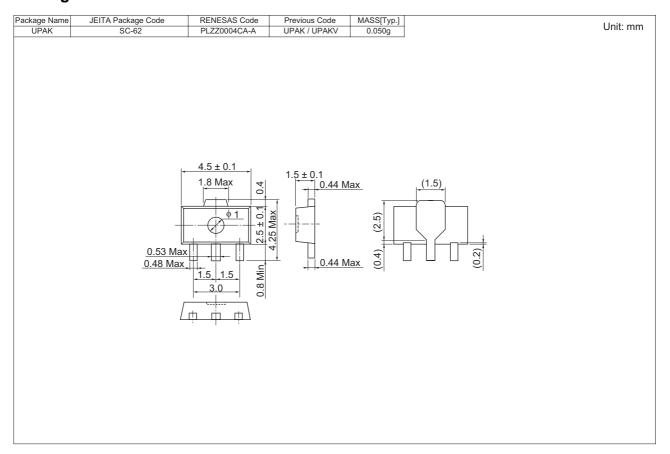
Main Characteristics







Package Dimensions



Ordering Information

| Part Name | Quantity | Shipping Container |
|---------------|----------|-----------------------------------|
| 2SK1697EYTL-E | 1000 pcs | φ178 mm Reel, 12 mm Emboss Taping |
| 2SK1697EYTR-E | | |

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.

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